

JUNCTION FIELD EFFECT TRANSISTOR 2SK3230

N-CHANNEL SILICON JUNCTION FIELD EFFECT TRANSISTOR FOR IMPEDANCE CONVERTER OF ECM

DESCRIPTION

The 2SK3230 is suitable for converter of ECM.

FEATURES

- · Compact package
- High forward transfer admittance 1000 μ S TYP. (lbss = 100 μ A) 1600 μ S TYP. (lbss = 200 μ A)
- Includes diode and high resistance at G S

ORDERING INFORMATION

PART NUMBER	PACKAGE		
2SK3230	SC-89 (TUSM)		

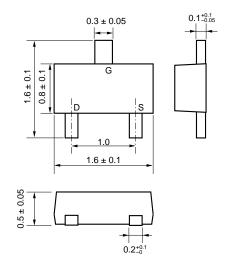
ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage Note1	VDSX	20	V
Gate to Drain Voltage	Vgdo	-20	V
Drain Current	lσ	10	mΑ
Gate Current	lg	10	mΑ
Total Power Dissipation Note2	PT	200	mW
Junction Temperature	T_j	125	°C
Storage Temperature	T _{stg}	-55 to +125	°C

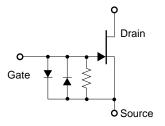


2. Mounted on ceramic substrate of 3.0 cm² x 0.64 mm

PACKAGE DRAWING (Unit: mm)



EQUIVALENT CIRCUIT



Remark Please take care of ESD (Electro Static Discharge) when you handle the device in this document.

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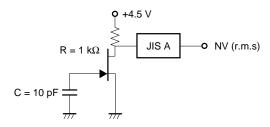
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	CHARACTERISTICS SYMBOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Cut-off Current	loss	V _{DS} = 5.0 V, V _{GS} = 0 V	40		600	μΑ
Gate Cut-off Voltage	V _{GS(off)}	$V_{DS} = 5.0 \text{V}, I_{D} = 1.0 \mu \text{A}$	-0.1		-1.0	V
Forward Transfer Admittance	y fs1	$V_{DS} = 5.0 \text{ V}, \text{ ID} = 30 \ \mu\text{A}, \text{ f} = 1.0 \text{ kHz}$	350			μS
Forward Transfer Admittance	y fs2	V _{DS} = 5.0 V, V _{GS} = 0 V, f = 1.0 kHz	350			μS
Input Capacitance	Ciss	V _{DS} = 5.0 V, V _{GS} = 0 V, f = 1.0 MHz		7.0	8.0	pF
Noise Voltage	NV	See Test Circuit		1.8	3.0	μV

IDSS RANK

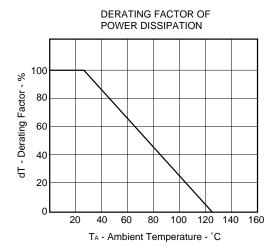
MARKING	J2	J3	J4	J5	J6	J7
I _{DSS} (μA)	40 to 70	60 to 110	90 to 180	150 to 300	200 to 450	300 to 600

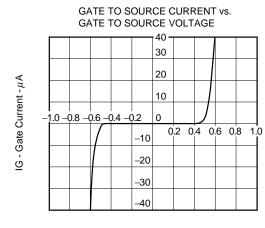
NOISE VOLTAGE TEST CIRCUIT



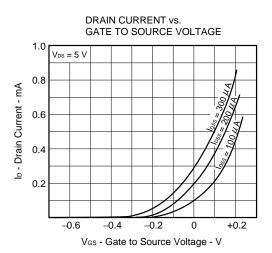
2

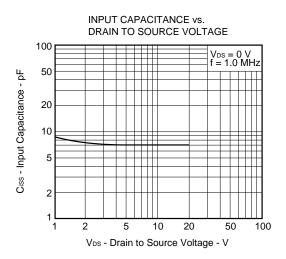
TYPICAL CHARACTERISTICS (TA = 25°C)



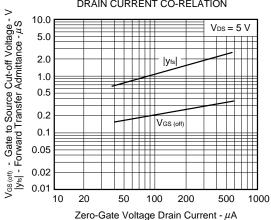


V_{GS} - Gate to Source Voltage - V





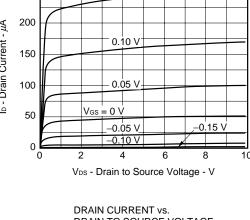
GATE TO SOURCE CUT-OFF VOLTAGE AND FORWARD TRANSFER ADMITTANCE vs. ZERO-GATE VOLTAGE DRAIN CURRENT CO-RELATION

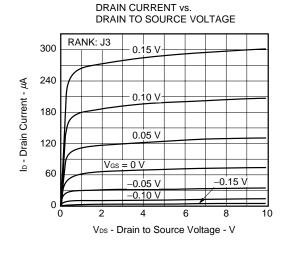


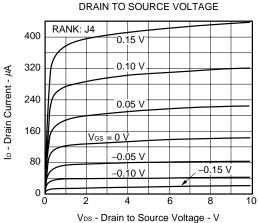
Data Sheet D15942EJ1V0DS 3

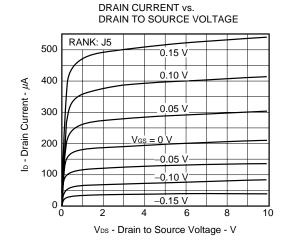
DRAIN TO SOURCE VOLTAGE RANK: J2 250 0.15 V 200 I_D - Drain Current - μA 0.10 V 150 0.05 V 100 $V_{GS} = 0 V$ 50 <u>-0.15</u> V -0.05 V_ –0.10 V 0 0 8 10

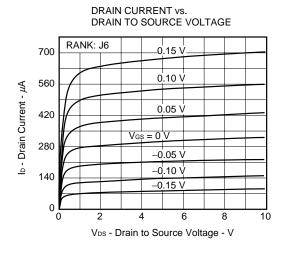
DRAIN CURRENT vs.

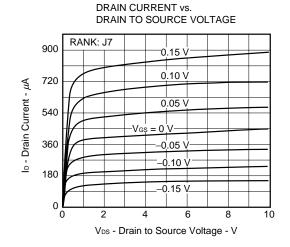












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